



WIDE BANDWIDTH AND MOS INPUT SINGLE OPERATIONAL AMPLIFIER

- LOW DISTORTION
- GAIN BANDWIDTH PRODUCT: 300MHz
- GAIN OF 2 STABILITY ■ SLEW RATE: 400V/µs
- VERY FAST SETTLING TIME: 60ns (0.1%)
- VERY HIGH INPUT IMPEDANCE

DESCRIPTION

The TSH321 is a wideband monolithic operational amplifier, requiring a minimum close loop gain of 2 for stability.

The TSH321 features extremely high input impedance (typically greater than $10^{12}\Omega$) allowing direct interfacing with high impedance sources.

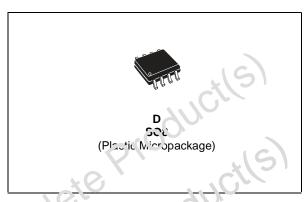
Low distortion, wide bandwidth and high linearity make this amplifier suitable for RF and video applications. Short circuit protection is provided by an internal current-limiting circuit.

The TSH321 has internal electrostatic discharge (ESD) protection circuits and fulfills MILSTD883C-Class2.

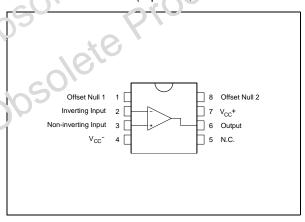
ORDER CODE

Part Number	Ton porature Range	Packane
TSH321I	-40°C, +125°C	•

D = Smai. O ול'הויף וּ ackage (SO) - alsף יי v vilal 'e in Tape & Reel (DT)

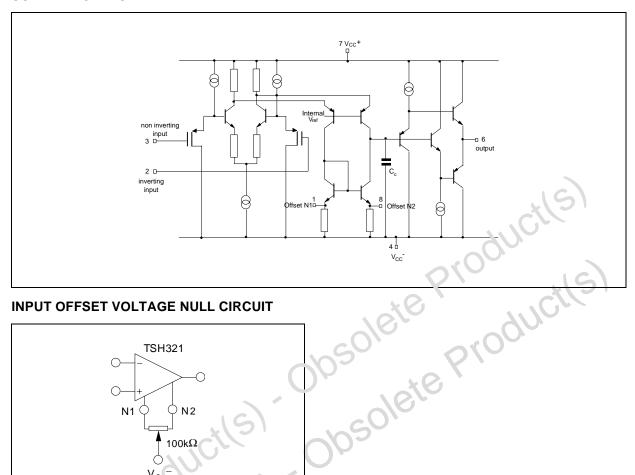


PIN CONNECTIONS (top view)

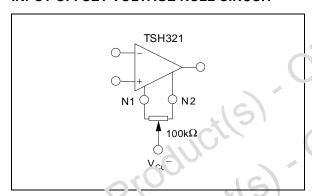


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SCHEMATIC DIAGRAM



INPUT OFFSET VOLTAGE NULL CIRCUIT



MAXIMUM PATINGS

Symbo	Parameter	Value	Unit
,\cc	Supply Voltage	±7	V
V _{id}	Differential Input Voltage	±5	V
V _i	Input Voltage	±5	V
I _{in}	Current On Offset Null Pins	±20	V
T _{oper}	Operating Free-Air Temperature range	-40 to +125	°C

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{cc}	Supply Voltage	±3 to ±6	V
V _{ic}	Common Mode Input Voltage Range	V _{CC} ⁻ to V _{CC} ⁺ -3	V

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ELECTRICAL CHARACTERISTICS

 $V_{CC} = \pm 5V$, $T_{amb} = 25$ °C (unless otherwise specified)

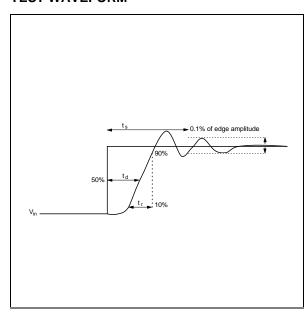
Symbol	Parameter	Min.	Тур.	Max.	Unit
V _{io}	Input Offset Voltage		0.5	10	mV
	$T_{min} \le T_{amb} \le T_{max}$			12	
DV_{io}	Input Offset Voltage Drift		10		μV/°C
	$T_{min} \le T_{amb} \le T_{max}$ Input Bias Current		10	200	
l _{ib}	•		2	300	pΑ
l _{io}	Input Offset Current		2	200	pA
I _{cc}	Supply Current, no load $ V_{CC} = \pm 5V $ $ V_{CC} = \pm 3V $		23 21	30 28	mA
	$V_{CC} = \pm 6V$ $T_{min} \le T_{amb} \le T_{max}$ $V_{CC} = \pm 5V$		25	40 3.7	5)
	Large Signal Voltage Gain Vo = ±2.5V			10,	
Avd	R _L = ∞	800	1300)	V/V
Avu	$R_L = 100\Omega$	300	850		V/V
	$R_L = 50\Omega$	200	350		16)
V_{icm}	Input Common Mode Voltage Range	-5 to +2	5.5 to +2.5		V
CMR	Common-mode Rejection Ratio $V_{ic} = V_{icm min.}$	60	100	1,10	dB
SVR	Supply Voltage Rejection Ratio $V_{CC} = \pm 5V$ to $\pm 3V$	50	70	70.	dB
	Output Voltage $R_L = 100\Omega$	±3	+3.5		
V_{o}	R _L = 5002	±2.8	-3.7 +3.3		V
۰0	11(= 33)	12.0	-3.5		v
	$T_{min} \le T_{amb} \le T_{max}$ $R_L = 100\Omega$ $R_L = 50\Omega$	±2.9 ±2.7			
I _o	Output Short Circuit Current Via = ±1V, Vo = 0V	±50	±100		mA
GBP	Gain Bandwidth Pr. Q.ICI $A_{VCL} = 100 \ R_L = 100 \Omega$, $C_L = 15pF$, $f = 7.5MHz$		300		MHz
SR	Slew Rate V_{in} =1V, A_{VCL} = 2, R_L = 100 Ω , C_L = 15pF	200	400		V/μs
	Equivalent Input Voltage Noise $R_s = 50\Omega$ $f_o = 1 \text{kHz}$		20		->///
e _n	$f_o = 1k0Hz$ $f_o = 100kHz$ $f_o = 1MHz$		18.2 18.1 18.2		nV/√Hz
K _{ov}	Overshoot $V_{in} = \pm 1V$, $A_{VCL} = 2$, $R_L = 100\Omega$, $C_L = 15pF$		15		%
t _s	Settling Time 0.1% ¹⁾ $V_{in} = \pm 1V, A_{VCL} = -1$		60		ns
t _r , t _f	Rise and Fall Time (see note 1) $V_{in} = \pm 100 \text{mV}, A_{VCL} = 2$		2		ns
t _d	Delay Time (see note 1) $V_{in} = \pm 100 \text{mV}, A_{VCL} = 2$		2		ns
φm	Phase Margin $A_{VM} = 2$, $R_L = 100\Omega$, $C_L = 15pF$		45		Degrees
THD	Total Harmonic Distortion $A_{VCL} = 10$, $f = 1$ kHz, $V_0 = \pm 2.5$ V, no load		0.02		%
FPB	Full Power Bandwidth $^{2)}$ Vo = 5Vpp, R _L = 100 Ω Vo = 2Vpp, R _L = 100 Ω		26 64		MHz

See test waveform figure

^{2.} Full power bandwidth =
SR
Π Vopp



TEST WAVEFORM



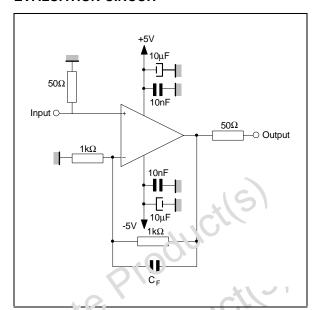
PRINTED CIRCUIT LAYOUT

As for any high frequency device, a few rules must be observed when designing the PCB to get the best performances from this high speed op amp.

From the most to the least important points :

- Each power supply lead has to be bypassed to ground with a 10n. ceramic capacitor very close to the Gevice and a 10μF tantalum capacitor.
- ☐ To provide low inductance and low resistance common teturn, use a ground plane or common point return for power and signal.
- □ All เอลช์s must be wide and as short as poss ible especially for op amp inputs. This is in

EVALUATION CIRCUIT



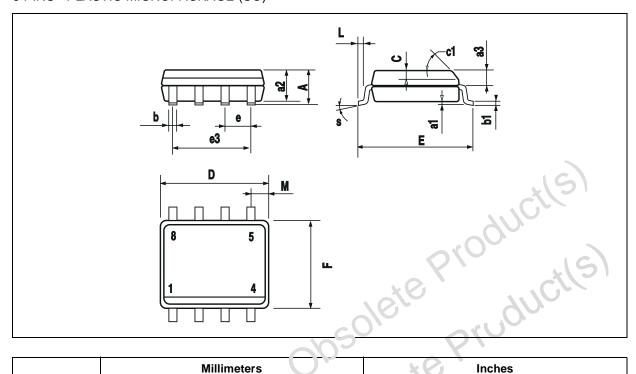
order to decrease parasitic capacitance and inductance.

- ☐ Use small resistor values to decrease time constant with parasitic capacitance.
- ☐ Choose component sizes as small as possible (SMD).
- On output, decrease capacitor load so as to avoid circuit stability being degraded which may cause oscillation. You can also add a serial resistor in order to minimise its influence.
- One can add in parallel with feedback resistor a few pF ceramic capacitor C_F adjusted to optimize the settling time.

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PACKAGE MECHANICAL DATA

8 PINS - PLASTIC MICROPACKAGE (SO)



Dim	Millimeters			Inches		
Dim.	Min.	Тур.	Max.	Min.	Тур.	Max.
Α		1(5)	1.75			0.069
a1	0.1	. C.L.	0.25	0.004		0.010
a2	41		1.65			0.065
a3	0.65		0.85	0.026		0.033
b	(1.35	115	0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
C * 6	0.25	110	0.5	0.010		0.020
C			45° ((typ.)		
D.	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
е	2, '	1.27			0.050	
e3)	3.81			0.150	
F	3.8		4.0	0.150		0.157
57	0.4		1.27	0.016		0.050
М			0.6			0.024
S	8° (max.)					

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